

## FNK N-Channel Enhancement Mode Power MOSFET

## **Description**

The FNK8601 uses advanced trench technology to provide excellent  $R_{\rm DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

#### **General Features**

V<sub>DS</sub> = 20V,I<sub>D</sub> =6A

 $R_{DS(ON)}$  < 26 m $\Omega$  @  $V_{GS}$ =2.5V

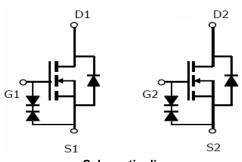
 $R_{DS(ON)}$  <22 m $\Omega$  @  $V_{GS}$ =4.5V

ESD Rating: 2000V HBM

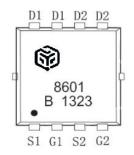
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

## **Application**

- PWM application
- ●Load switch



Schematic diagra



Marking and pin assignment

### **Package Marking And Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8601	FNK8601	PDFN3*3-8L	Ø180mm	8mm	3000 units

## Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	20	V	
Gate-Source Voltage	V <sub>G</sub> s	±12	V	
Drain Current-Continuous	I <sub>D</sub>	6	Α	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	25	Α	
Maximum Power Dissipation	P <sub>D</sub>	P <sub>D</sub> 1.5		
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$	

#### **Thermal Characteristic**

I nermal Resistance, Junction-to-Ambient (Note 2)		R <sub>0JA</sub>	83.3	°C/W
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## **Electrical Characteristics (TA=25** ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μΑ

FNK-Semiconductor 1/7 Rev.1.1



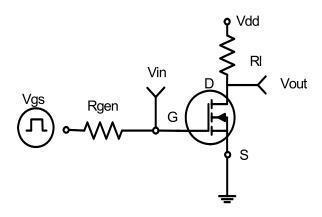
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.55	0.7	0.95	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A	-	17	22	mΩ
Diali-Source Oil-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A	-	20	25	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =7A		20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/=10\/ \/=0\/	-	1150	ı	PF
Output Capacitance	Coss	$V_{DS}$ =10V, $V_{GS}$ =0V, F=1.0MHz	-	185	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	1-1.0IVII 12	-	145	ı	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	6		nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10V, $R_L$ =1.35 $\Omega$	-	13		nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =5 $V$ , $R_{GEN}$ =3 $\Omega$	-	52		nS
Turn-Off Fall Time	t <sub>f</sub>		-	16		nS
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V,I <sub>D</sub> =7A,	-	15		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10V, I_D = 7A,$ $V_{GS} = 4.5V$	-	0.8	ı	nC
Gate-Drain Charge	$Q_{gd}$	VGS-4.5V	-	3.2	ı	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7	Α

## Notes:

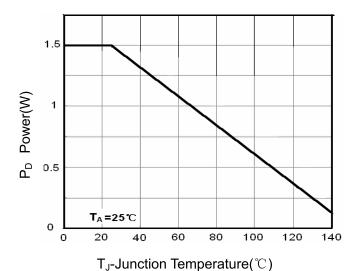
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production



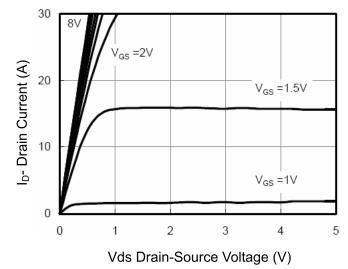
## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



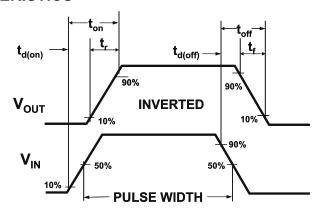
**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output CHARACTERISTICS** 



**Figure 2:Switching Waveforms** 

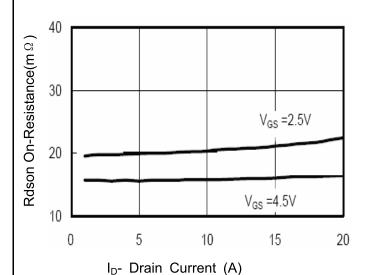


Figure 6 Drain-Source On-Resistance

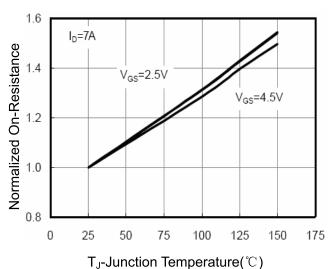
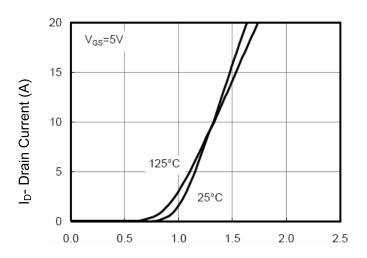


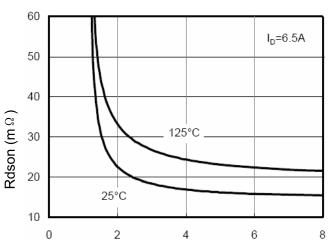
Figure 8 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

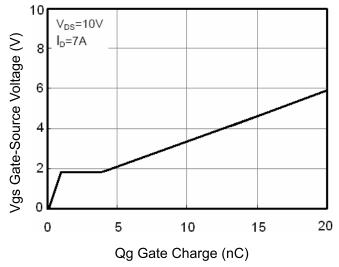
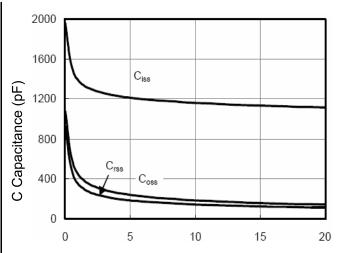


Figure 11 Gate Charge



Vds Drain-Source Voltage (V)

Figure 8 Capacitance vs Vds

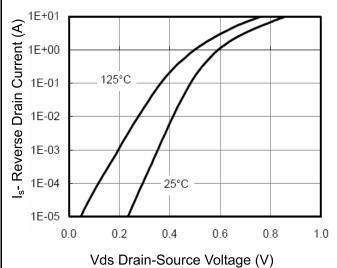


Figure 10 Capacitance vs Vds

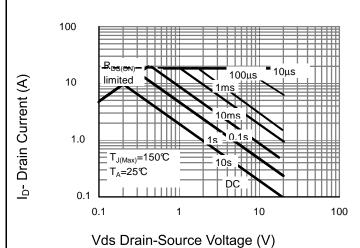
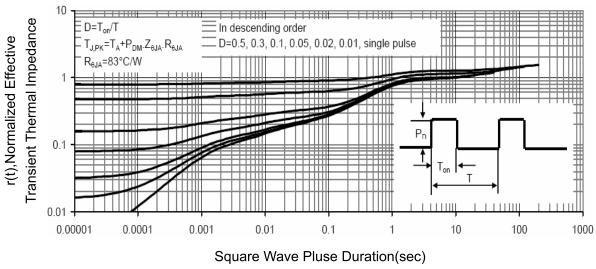


Figure 13 Safe Operation Area

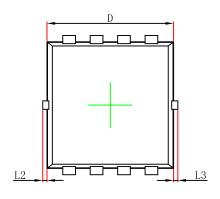


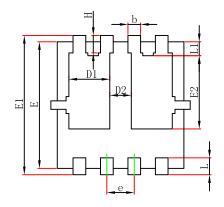


**Figure 14 Normalized Maximum Transient Thermal Impedance** 



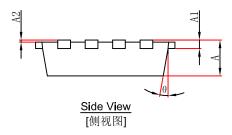
# PDFNWB(3.3×3.3)-8L-B(P0.65T0.80) PACKAGE OUTLINE DIMENSIONS





Top View [顶视图]

Bottom View [背视图]



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	0.650	0.850	0.026	0.033		
A1	0.152	REF.	0.006 REF.			
A2	0~0	).05	0~0.002			
D	2.900	3.100	0.114	0.122		
D1	0.935	1.135	0.037	0.045		
D2	0.280	0.480	0.011	0.019		
E	2.900	3.100	0.114	0.122		
E1	3.150	3.450	0.124	0.136		
E2	1.535	1.935	0.060	0.076		
b	0.200	0.400	0.008	0.016		
е	0.550	0.750	0.022	0.030		
L	0.300	0.500	0.012	0.020		
L1	0.180	0.480	0.007	0.019		
L2	0~0.100		0~0.004			
L3	0~0.100		0~0	.004		
Н	0.315	0.515	0.012	0.020		
θ	9°	13°	9°	13°		



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